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Harry J. Levinson
Mircea V. Dusa
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Yao-Ching Ku, Taiwan Semiconductor Manufacturing Company, Ltd. (Taiwan)
Kafai Lai, IBM Microelectronics Division (USA)
SukJoo Lee, Samsung Electronics Company, Ltd. (South Korea)
Koichi Matsumoto, Nikon Corporation (Japan)
Wilhelm Maurer, Infineon Technologies AG (Germany)
Ken Ozawa, Sony Atsugi Technology Center (Japan)
Sam Sivakumar, Intel Corporation (USA)
Bruce W. Smith, Rochester Institute of Technology (USA)
Akiyoshi Suzuki, Canon, Inc. (Japan)
Geert Vandenberghe, IMEC (Belgium)

Session Chairs

- 1 Keynote Session
Harry J. Levinson, Advanced Micro Devices, Inc. (USA)
Mircea V. Dusa, ASML US, Inc. (USA)
- 2 Double Masking I
Geert Vandenberghe, IMEC (Belgium)
Willard E. Conley, Freescale Semiconductor, Inc. (USA)
- 3 Double Masking II
Tomoyuki Matsuyama, Nikon Corporation (Japan)
Geert Vandenberghe, IMEC (Belgium)

- 4 Low-k1 Lithography I
Tatsuhiko Higashiki, Toshiba Corporation (Japan)
Kafai Lai, IBM Microelectronics Division (USA)
- 5 Low-k1 Lithography II
Wilhelm Maurer, Infineon Technologies AG (Germany)
Ken Ozawa, Sony Atsugi Technology Center (Japan)
- 6 Double Masking III
Sam Sivakumar, Intel Corporation (USA)
Pary Baluswamy, Micron Technology, Inc. (USA)
- 7 Simulation I
Kafai Lai, IBM Microelectronics Division (USA)
Nigel R. Farrar, Cymer, Inc. (USA)
- 8 Simulation II
Akiyoshi Suzuki, Canon, Inc. (Japan)
Tatsuhiko Higashiki, Toshiba Corporation (Japan)
- 9 High Index Immersion Lithography
Willard E. Conley, Freescale Semiconductor, Inc. (USA)
Sam Sivakumar, Intel Corporation (USA)
- 10 Process I
Nigel R. Farrar, Cymer, Inc. (USA)
Wilhelm Maurer, Infineon Technologies AG (Germany)
- 11 OPC and Mask Technology
Willard E. Conley, Freescale Semiconductor, Inc. (USA)
Bruce W. Smith, Rochester Institute of Technology (USA)
- 12 Process II
Roger H. French, DuPont Company (USA)
Pary Baluswamy, Micron Technology, Inc. (USA)
- 13 Lithography Tools I
Willard E. Conley, Freescale Semiconductor, Inc. (USA)
Tatsuhiko Higashiki, Toshiba Corporation (Japan)
- 14 Lithography Tools II
Ken Ozawa, Sony Atsugi Technology Center (Japan)
Roger H. French, DuPont Company (USA)